Michael A Scarpulla

List of Publications by Year in descending order

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156
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186265
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h-index

197818 49 g-index

157 all docs 157 docs citations

157 times ranked

3290 citing authors

#	Article	lF	CITATIONS
1	Quantifying the Environmental Sensitivity of SSTDR Signals for Monitoring PV Strings. IEEE Journal of Photovoltaics, 2022, 12, 381-387.	2.5	2
2	Anomaly Detection of Disconnects Using SSTDR and Variational Autoencoders. IEEE Sensors Journal, 2022, 22, 3484-3492.	4.7	4
3	Effect of extended defects on photoluminescence of gallium oxide and aluminum gallium oxide epitaxial films. Scientific Reports, 2022, 12, 3243.	3.3	16
4	Electronic and ionic conductivity in \hat{I}^2 -Ga2O3 single crystals. Journal of Applied Physics, 2022, 131, .	2.5	5
5	Spread Spectrum Time Domain Reflectometry With Lumped Elements on Asymmetric Transmission Lines. IEEE Sensors Journal, 2021, 21, 921-929.	4.7	16
6	Finding Faults in PV Systems: Supervised and Unsupervised Dictionary Learning With SSTDR. IEEE Sensors Journal, 2021, 21, 4855-4865.	4.7	15
7	Detection and Localization of Damaged Photovoltaic Cells and Modules Using Spread Spectrum Time Domain Reflectometry. IEEE Journal of Photovoltaics, 2021, 11, 195-201.	2.5	11
8	Impact of high-dose gamma-ray irradiation on electrical characteristics of N-polar and Ga-polar GaN $\mbox{\sc i>pa}\mbox{\sc i>n} diodes. AIP Advances, 2021, 11, .$	1.3	5
9	Oxygen annealing induced changes in defects within \hat{l}^2 -Ga ₂ O ₃ epitaxial films measured using photoluminescence. Journal Physics D: Applied Physics, 2021, 54, 174004.	2.8	11
10	Optical Characterization of Gallium Oxide $\hat{l}\pm$ and \hat{l}^2 Polymorph Thin-Films Grown on c-Plane Sapphire. Journal of Electronic Materials, 2021, 50, 2990-2998.	2.2	9
11	Quantifying the Window of Uncertainty for SSTDR Measurements of a Photovoltaic System. IEEE Sensors Journal, 2021, 21, 9890-9899.	4.7	5
12	N-type doping of low-pressure chemical vapor deposition grown \hat{l}^2 -Ga2O3 thin films using solid-source germanium. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	14
13	Differences in electrical responses and recovery of GaN p+n diodes on sapphire and freestanding GaN subjected to high dose 60Co gamma-ray irradiation. Journal of Applied Physics, 2021, 129, .	2.5	5
14	Detection and Localization of Disconnections in a Large-Scale String of Photovoltaics Using SSTDR. IEEE Journal of Photovoltaics, 2021, 11, 1097-1104.	2.5	7
15	In Situ Dielectric Al ₂ O ₃ /βâ€Ga ₂ O ₃ Interfaces Grown Using Metal–Organic Chemical Vapor Deposition. Advanced Electronic Materials, 2021, 7, 2100333.	5.1	17
16	Growth and characterization of metalorganic vapor-phase epitaxy-grown \hat{I}^2 -(Al _x) Tj ETQq0 0 0 rgBT channels. Applied Physics Express, 2021, 14, 025501.	/Overlock 2.4	10 Tf 50 147 40
17	Environmentally friendly thermoelectric sulphide Cu ₂ ZnSnS ₄ single crystals achieving a 1.6 dimensionless figure of merit <i>ZT</i> . Journal of Materials Chemistry A, 2021, 9, 15595-15604.	10.3	17
18	Continuous-wave laser annealing of metallic layers for CuInSe2 solar cell applications: effect of preheating treatment on grain growth. RSC Advances, 2020, 10, 584-594.	3.6	2

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19	Detection and Localization of Disconnections in PV Strings Using Spread-Spectrum Time-Domain Reflectometry. IEEE Journal of Photovoltaics, 2020, 10, 236-242.	2.5	19
20	Cadmium Selective Etching in CdTe Solar Cells Produces Detrimental Narrow-Gap Te in Grain Boundaries. ACS Applied Energy Materials, 2020, 3, 1749-1758.	5.1	6
21	Compensation in $(2\hat{A}^{-}01)$ homoepitaxial $i^2<$ Ga2O3 thin films grown by metalorganic vapor-phase epitaxy. Journal of Applied Physics, 2020, 128, .	2.5	13
22	Defect states and their electric field-enhanced electron thermal emission in heavily Zr-doped 	3.3	13
23	Growth and Characterization of Arsenic-Doped CdTe1â^'xSex Single Crystals Grown by the Cd-Solvent Traveling Heater Method. Journal of Electronic Materials, 2020, 49, 6971-6976.	2.2	2
24	On the origin of red luminescence from iron-doped $\langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga2O3 bulk crystals. Applied Physics Letters, 2020, 117, .	3.3	26
25	Measurement of Capacitance Using Spread Spectrum Time Domain Reflectometry (SSTDR) and Dictionary Matching. IEEE Sensors Journal, 2020, 20, 10102-10109.	4.7	11
26	A Model for SSTDR Signal Propagation Through Photovoltaic Strings. IEEE Journal of Photovoltaics, 2020, 10, 1846-1852.	2.5	3
27	Synthesis and Characterization of Largeâ€Area Nanometerâ€Thin βâ€Ga ₂ O ₃ Films from Oxide Printing of Liquid Metal Gallium. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1901007.	1.8	16
28	REFLECTOMETRY ON ASYMMETRIC TRANSMISSION LINE SYSTEMS. Progress in Electromagnetics Research M, 2020, 89, 121-130.	0.9	5
29	An Overview of Spread Spectrum Time Domain Reflectometry Responses to Photovoltaic Faults. IEEE Journal of Photovoltaics, 2020, 10, 844-851.	2.5	25
30	Delta-doped $\langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle$ thin films and $\langle i \rangle \hat{l}^2 \langle i \rangle$ -(Al $\langle sub \rangle 0.26 \langle sub \rangle 0.74 \langle sub \rangle) \langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle i \rangle$ -Ga $\langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle sub \rangle 2 \langle sub \rangle 0 \langle sub \rangle 3 \langle sub \rangle \langle i \rangle \hat{l}^2 \langle sub \rangle 2 \langle sub $	sub2>43 <td>ıb>38</td>	ıb>38
31	Schottky Barrier Height Engineering in <i>\hat{l}^2</i> -Ga ₂ O ₃ Using SiO ₂ Interlayer Dielectric. IEEE Journal of the Electron Devices Society, 2020, 8, 286-294.	2.1	32
32	Comparison of Sb, As, and P doping in Cd-rich CdTe single crystals: Doping properties, persistent photoconductivity, and long-term stability. Applied Physics Letters, 2020, 116 , .	3.3	18
33	The anisotropic quasi-static permittivity of single-crystal <i>\hat{l}^2</i> -Ga2O3 measured by terahertz spectroscopy. Applied Physics Letters, 2020, 117, .	3.3	27
34	Postprocessing for Improved Accuracy and Resolution of Spread Spectrum Time-Domain Reflectometry., 2019, 3, 1-4.		19
35	Freestanding Thinâ€Films: Waterâ€Assisted Liftoff of Polycrystalline CdS/CdTe Thin Films Using Heterogeneous Interfacial Engineering (Adv. Mater. Interfaces 14/2019). Advanced Materials Interfaces, 2019, 6, 1970095.	3.7	0
36	Spread spectrum time-domain reflectometry for detecting and locating capacitive impedances. AIP Conference Proceedings, 2019, , .	0.4	5

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37	Observation and Implications of Composition Inhomogeneity Along Grain Boundaries in Thin Film Polycrystalline CdTe Photovoltaic Devices. Advanced Materials Interfaces, 2019, 6, 1900152.	3.7	5
38	Waterâ€Assisted Liftoff of Polycrystalline CdS/CdTe Thin Films Using Heterogeneous Interfacial Engineering. Advanced Materials Interfaces, 2019, 6, 1900300.	3.7	7
39	Arsenic doped Cd-rich CdTe: equilibrium doping limit and long lifetime for high open-circuit voltage solar cells greater than 900 mV. Applied Physics Express, 2019, 12, 081002.	2.4	6
40	Manifestation of Kinetic Inductance in Terahertz Plasmon Resonances in Thin-Film Cd ₃ As ₂ . ACS Nano, 2019, 13, 4091-4100.	14.6	24
41	Improving the grain size of \$\$ext {Cu}_{2}ext {ZnSnS}_{4}\$\$ Cu 2 ZnSnS 4 thin films by annealing thermally evaporated Cu–. Journal of Materials Science: Materials in Electronics, 2019, 30, 4931-4935.	2.2	2
42	Applicability of SSTDR Analysis of Complex Loads. , 2019, , .		4
43	Grain Growth in CdTe Films During CdCl ₂ Treatment: TeCl ₄ Theory., 2019,,.		2
44	Signal Propagation Through Piecewise Transmission Lines for Interpretation of Reflectometry in Photovoltaic Systems. IEEE Journal of Photovoltaics, 2019, 9, 506-512.	2.5	14
45	Photoassisted physical vapor epitaxial growth of semiconductors: a review of light-induced modifications to growth processes. Journal Physics D: Applied Physics, 2018, 51, 023001.	2.8	6
46	Mapping carrier lifetime variations in polycrystalline CdTe thin films using confocal microscopy. , 2018, , .		1
47	Strong terahertz plasmonic resonances in thin-film Cd <inf>3</inf> As <inf>2</inf> : a three-dimensional Dirac semimetal., 2018, , .		0
48	Fault Detection In PV Strings Using SSTDR. , 2018, , .		6
49	Spread Spectrum Time Domain Reflectometry for Complex Impedances: Application to PV Arrays. , 2018, , .		13
50	Incident wavelength and polarization dependence of spectral shifts in \hat{l}^2 -Ga2O3 UV photoluminescence. Scientific Reports, 2018, 8, 18075.	3.3	62
51	Thin Film Solar Cells Based on n-type Polycrystalline CdTe Absorber. , 2018, , .		3
52	Ultrafast terahertz modulator based on metamaterial-integrated WSe2 thin-films. , 2018, , .		0
53	Doping properties of cadmium-rich arsenic-doped CdTe for application of single crystal solar cell. , 2018, , .		0
54	Enhancement in surface mobility and quantum transport of Bi2â^'xSbxTe3â^'ySey topological insulator by controlling the crystal growth conditions. Scientific Reports, 2018, 8, 17290.	3.3	17

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55	Dramatic Recrystallization During CdCl <inf>2</inf> Treatment of Evaporated CdTe Thin Filmsa. , 2018, , .		0
56	Defect properties of Na and K in Cu2ZnSnS4 from hybrid functional calculation. Journal of Applied Physics, 2018, 124, 165701.	2.5	14
57	Effects of excess carriers on charged defect concentrations in wide bandgap semiconductors. Journal of Applied Physics, 2018, 123, .	2.5	7
58	High p-type doping, mobility, and photocarrier lifetime in arsenic-doped CdTe single crystals. Applied Physics Letters, 2018, 112, .	3.3	33
59	Growth and characterization of Arsenic doped CdTe single crystals grown by Cd-solvent traveling-heater method. Journal of Crystal Growth, 2017, 467, 6-11.	1.5	20
60	Laser annealing of electrodeposited CulnSe2semiconductor precursors: experiment and modeling. Journal of Materials Chemistry C, 2017, 5, 1336-1345.	5.5	6
61	Cu 2 ZnSnSe 4 Photovoltaic Absorber Layers Evaluated by Transmission Xâ€Ray Microscopy Tomography: Composition Fluctuations on the Length Scale of Grains. Solar Rrl, 2017, 1, 1600024.	5.8	0
62	Calculation of point defect concentration in Cu2ZnSnS4: Insights into the high-temperature equilibrium and quenching. Journal of Applied Physics, 2017, 122, .	2.5	5
63	CdTe _{1â^'<i>x</i>} S _{<i>x</i>} (<i>x</i>)  ⩽  0.05) thin films synthesisolution deposition and annealing. Materials Research Express, 2017, 4, 115904.	ized by aq	ueous
64	Doping properties of cadmium-rich arsenic-doped CdTe single crystals: Evidence of metastable AX behavior. Applied Physics Letters, 2017, 111, .	3.3	27
65	Group-V doping impact on Cd-rich CdTe single crystals grown by traveling-heater method. , 2017, , .		0
66	Large grain growth in Cu2ZnSnS4 thin films in the absence of Na using rapid thermal annealing. , 2017, , .		0
67	Cation ratio fluctuations in Cu ₂ ZnSnS ₄ at the 20 nm length scale investigated by analytical electron microscopy. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2392-2399.	1.8	11
68	Minority carrier electron traps in CZTSSe solar cells characterized by DLTS and DLOS., 2016,,.		1
69	A method for depositing CdTe from aqueous solution. , 2016, , .		0
70	Near infrared laser CdCl <inf>2</inf> heat treatment for CdTe solar cells. , 2016, , .		1
71	Near infrared laser annealing of CdTe and $\langle i \rangle$ in-situ $\langle i \rangle$ measurement of the evolution of structural and optical properties. Journal of Applied Physics, 2016, 119, .	2.5	4
72	Voltage-Induced Transients in Methylammonium Lead Triiodide Probed by Dynamic Photoluminescence Spectroscopy. Journal of Physical Chemistry C, 2016, 120, 7893-7902.	3.1	24

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73	Na-doped Cu2ZnSnS4 single crystal grown by traveling-heater method. Journal of Crystal Growth, 2016, 453, 119-123.	1.5	14
74	Suppression of compensating native defect formation during semiconductor processing via excess carriers. Scientific Reports, 2016, 6, 27954.	3.3	36
75	Characterization of Sputtered CdTe Thin Films with Electron Backscatter Diffraction and Correlation with Device Performance. Microscopy and Microanalysis, 2015, 21, 927-935.	0.4	14
76	Interplay between surface preparation and device performance in CZTSSe solar cells: Effects of KCN and NH4OH etching. Solar Energy Materials and Solar Cells, 2015, 136, 78-85.	6.2	38
77	Reduction of Fermi level pinning and recombination at polycrystalline CdTe surfaces by laser irradiation. Journal of Applied Physics, 2015, 117, 225301.	2.5	3
78	Laser processing for thin film chalcogenide photovoltaics: a review and prospectus. Journal of Photonics for Energy, 2015, 5, 050999.	1.3	33
79	Te-rich CdTe surface by pulsed UV laser treatment for ohmic back contact formation. , 2014, , .		2
80	Strain tuning of native defect populations: The case of Cu2ZnSn(S,Se)4. APL Materials, 2014, 2, 012110.	5.1	8
81	Single Second Laser Annealed CulnSe2 Semiconductors from Electrodeposited Precursors as Absorber Layers for Solar Cells. Journal of Physical Chemistry C, 2014, 118, 1451-1460.	3.1	20
82	The importance of Se partial pressure in the laser annealing of CuInSe $\!$ inf $\!$ 2 $\!$ /linf $\!$ electrodeposited precursors. , 2014, , .		2
83	Pulsed laser induced ohmic back contact in CdTe solar cells. Applied Physics Letters, 2014, 104, 141604.	3.3	13
84	Surface stoichiometry of pulsed ultraviolet laser treated polycrystalline CdTe. Journal of Applied Physics, 2014, 116, 013506.	2.5	6
85	Effects of sodium on electrical properties in Cu2ZnSnS4 single crystal. Applied Physics Letters, 2014, 104, .	3.3	113
86	Design principles for light trapping in thin silicon films with embedded dielectric nanoparticles. Progress in Photovoltaics: Research and Applications, 2013, 21, 319-325.	8.1	12
87	Model of native point defect equilibrium in Cu2ZnSnS4 and application to one-zone annealing. Journal of Applied Physics, 2013, 114, 124501.	2.5	48
88	Effect of metal coating on machinability of high purity germanium using wire electrical discharge machining. Journal of Materials Processing Technology, 2013, 213, 811-817.	6.3	11
89	Modeling Cu ₂ ZnSnS ₄ (CZTS) solar cells with kesterite and stannite phase variation. Proceedings of SPIE, 2013, , .	0.8	4
90	Enhanced light absorption in thin film solar cells with embedded dielectric nanoparticles: Induced texture dominates Mie scattering. Applied Physics Letters, 2013, 102, .	3.3	8

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91	Pulsed UV laser annealing of polycrystalline CdTe. Proceedings of SPIE, 2013, , .	0.8	5
92	Continuous wave solid phase laser annealing of single-pot electrodeposited CuInSe2 thin films: Effects of Cu/In stoichiometry. Journal of Applied Physics, 2013, 114, .	2.5	9
93	Study of point defects in ns pulsed-laser annealed CuInSe2 thin films. , 2013, , .		2
94	Crystallographic study of phases present in CuInSe ₂ absorber layers produced by laser annealing co-electrodeposited precursors. Proceedings of SPIE, 2013, , .	0.8	4
95	Pulsed and continuous wave solid phase laser annealing of electrodeposited CulnSe ₂ thin films. Proceedings of SPIE, 2012, , .	0.8	8
96	Equivalent deflection angle of textured surfaces. , 2012, , .		0
97	Effects of annealing in sulfur vapor on electrodeposited CuInSe2 films. , 2012, , .		1
98	The correlation of performance in CdTe photovoltaics with grain boundaries. , 2012, , .		6
99	Exact field solution to guided wave propagation in lossy thin films. Proceedings of SPIE, 2012, , .	0.8	3
100	Grain growth study of electrochemically deposited CuInSe2 by rapid thermal annealing in sulfur atmosphere. Proceedings of SPIE, 2012, , .	0.8	3
101	Study of point defects in ns pulsed-laser annealed CuInSe2 thin films. , 2012, , .		0
102	Temperature dependent conductivity of polycrystalline Cu2ZnSnS4 thin films. Applied Physics Letters, 2012, 100, .	3.3	86
103	Synthesis of Ge1â^'x Sn x Alloy Thin Films Using Ion Implantation and Pulsed Laser Melting (II-PLM). Journal of Electronic Materials, 2012, 41, 837-844.	2.2	10
104	Integrated non-III-nitride/III-nitride tandem solar cell. , 2011, , .		0
105	Enhanced light absorption in thin-film silicon solar cells by scattering from embedded dielectric nanoparticles., 2011,,.		1
106	Detection of ZnS phases in CZTS thin-films by EXAFS. , 2011, , .		0
107	Exact field solution to guided wave propagation in lossy thin films. Optics Express, 2011, 19, 20159.	3.4	11
108	Pulsed laser processing of electrodeposited CulnSe <inf>2</inf> Photovoltaic absorber thin films. , 2011, , .		3

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109	SnS thin-films by RF sputtering at room temperature. Thin Solid Films, 2011, 519, 7421-7424.	1.8	224
110	Grain Size and Texture of Cu2ZnSnS4 Thin Films Synthesized by Cosputtering Binary Sulfides and Annealing: Effects of Processing Conditions and Sodium. Journal of Electronic Materials, 2011, 40, 2214-2221.	2.2	122
111	Electron backscatter diffraction and photoluminescence of sputtered CdTe thin films., 2011,,.		2
112	Ferromagnetic Resonance Study of Galâ^'x Mn x As Fabricated onÂ(311) GaAs Wafers by Mn Ion Implantation and Pulsed-Laser Melting. Journal of Superconductivity and Novel Magnetism, 2010, 23, 87-90.	1.8	3
113	Growth of embedded ErAs nanorods on (411)A and (411)B GaAs by molecular beam epitaxy. Journal of Crystal Growth, 2010, 312, 2089-2092.	1.5	14
114	Pulsed Laser Processing of Electrodeposited CulnSe ₂ Photovoltaic Absorber Thin Films. Materials Research Society Symposia Proceedings, 2010, 1268, 1.	0.1	10
115	Investigating sputtered Cu <inf>2</inf> Si <inf>3</inf> Sn <inf>x</inf> 330., .	t;	0
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